L Number	Hits	Search Text	DB	Time stamp
1	108981	buried	USPAT;	2004/09/19 16:13
			US-PGPUB;	2004/07/17 10:13
			ло	
2	5541	p-well\$1 same n-well\$1	USPAT;	2004/09/19 16:14
			US-PGPUB;	200 1103717 10:11
			ЛРО	
3	21222	well\$1 with (conductivity)	USPAT;	2004/09/19 16:15
			US-PGPUB;	
			JPO ´	
4	155371	(potential or voltage\$1) near2 differen\$3	USPAT;	2004/09/19 16:16
			US-PGPUB;	
			JPO	
5	1122235	semiconduct\$3 or silicon	USPAT;	2004/09/19 16:17
			US-PGPUB;	
			ЈРО	
6	164757	implant\$3	USPAT;	2004/09/19 16:17
			US-PGPUB;	
	4004		ЈРО	
7	4006	buried and ((p-well\$1 same n-well\$1) or (well\$1 with (conductivity)))	USPAT;	2004/09/19 16:17
		and (semiconduct\$3 or silicon)	US-PGPUB;	
	536	(1 1 1 1 // 1101	JPO	
8	576	(buried and ((p-well\$1 same n-well\$1) or (well\$1 with (conductivity)))	USPAT;	2004/09/19·16:18
		and (semiconduct\$3 or silicon)) and implant\$3 and ((potential or	US-PGPUB;	
9	4319	voltage\$1) near2 differen\$3) third adj2 well\$1	JPO	
3	4319	dird adj2 wen51	USPAT;	2004/09/19 16:19
			US-PGPUB;	
10	5	((buried and ((p-well\$1 same n-well\$1) or (well\$1 with (conductivity)))	JPO USPAT;	2004/09/19 16:20
		and (semiconduct\$3 or silicon)) and implant\$3 and ((potential or	US-PGPUB;	2004/09/19 10.20
		voltage\$1) near2 differen\$3)) not "10"	ло ЛРО	
11	42	((buried and ((p-well\$1 same n-well\$1) or (well\$1 with (conductivity)))	USPAT;	2004/09/19 16:24
1		and (semiconduct\$3 or silicon)) and implant\$3 and ((potential or	US-PGPUB;	2004/03/13 10.24
		voltage\$1) near2 differen\$3)) and (third adj2 well\$1)	ло ЛРО	
12	534	((buried and ((p-well\$1 same n-well\$1) or (well\$1 with (conductivity)))	USPAT;	2004/09/19 16:24
}		and (semiconduct\$3 or silicon)) and implant\$3 and ((potential or	US-PGPUB;	
1		voltage\$1) near2 differen\$3)) not (((buried and ((p-well\$1 same	јро	
	İ	n-well\$1) or (well\$1 with (conductivity))) and (semiconduct\$3 or		
		silicon)) and implant\$3 and ((potential or voltage\$1) near2 differen\$3))		
		and (third adj2 well\$1))		